

L Number	Hits	Search Text	DB	Time stamp
-	4	'gate oxide' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 07:29
-	7	@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 07:29
-	1	@ad<=20020219 and 'ONO' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 08:28
-	10	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 08:32
-	52	(438/954).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:24
-	245	(438/593).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:26
-	627	(438/770).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:31
-	481	(438/264).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:27
-	208	(438/594).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:27
-	518	(438/275).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:28
-	323	(438/199).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:28
-	91	(438/477).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:28
-	77	(438/216).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:28
-	577	(438/287).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:29

-	166	(438/783).cccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/24 13:29
-	8	'gate oxide' and 'in-situ steam generation' or 'LP-RTP'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:36
-	2	("5324675").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:11
-	1	'thin film transistor' and 'gate oxide' and 'in-situ steam generation' or 'LP-RTP'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:49
-	27216	@ad<=20020219 and 'TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:35
-	0	(@ad<=20020219 and 'TFT') and 'oxide' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:38
-	0	(@ad<=20020219 and 'TFT') and 'oxide' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:38
-	0	(@ad<=20020219 and 'TFT') and 'oxide' and 'LP-RTP'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:39
-	226	(@ad<=20020219 and 'TFT') and 'floating gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:39
-	169	(@ad<=20020219 and 'TFT') and 'oxide' and 'floating gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:55
-	1	'tft' and 'in-situ steam generation' or 'LP-RTP'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 11:12
-	0	'tft' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 10:51
-	64	(@ad<=20020219 and 'TFT') and 'oxide layer' and 'floating gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 11:04
-	571	(438/149).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 11:05

-	11	@ad<=20020214 and (438/149).ccls. and 'floating gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 11:06
-	3585	((438/294) or (438/954) or (438/593-594) or (438/770) or (438/264) or (438/275) or (438/199) or (438/477) or (438/216) or (438/287) or (438/783)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 09:50
-	15	@ad<=20020219 and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 11:57
-	29	@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 12:54
-	27	@ad<=20020219 and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 12:07
-	2	@ad<=20020219 and 'low pressure rapid thermal process'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/26 12:17
-	416	@ad<=20020219 and 'TFT' and 'ONO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 07:12
-	0	@ad<=20020219 and 'TFT' and 'ONO' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 07:12
-	0	@ad<=20020219 and 'TFT' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 07:13
-	71	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 08:16
-	2	("6525384").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 09:48
-	2	"20030155582"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:45
-	2	'TFT' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:04
-	2	("5700699").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:59

-	0	'thin film transistor' near 'issg'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:04
-	0	'tft' near 'issg'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:04
-	0	'TFT' near 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:30
-	0	'TFT' near 'free radical enhanced rapid thermal oxidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:31
-	0	'TFT' same 'free radical enhanced rapid thermal oxidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:32
-	1	'TFT' and 'free radical enhanced rapid thermal oxidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:32